

Fig. 1 is a cross-sectional view of a semiconductor device. The device is formed on a substrate 10. A layer 11 is formed on the substrate 10. A layer 12 is formed on the layer 11. A layer 13 is formed on the layer 12. A layer 14 is formed on the layer 13. A layer 21 is formed on the layer 14. A layer 22 is formed on the layer 21. A layer 23 is formed on the layer 22. A layer 231 is formed on the layer 23. A layer 31 is formed on the layer 231. A layer 32 is formed on the layer 31. A layer 33 is formed on the layer 32. The device includes a p+ region (13) and an n- region (14).

Drawing
Correction approved
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